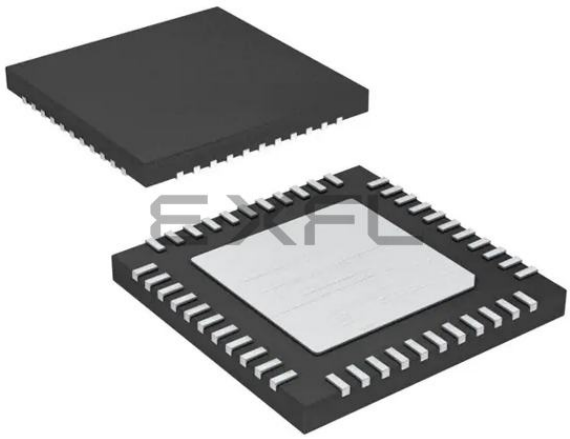

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	PIC
Core Size	8-Bit
Speed	25MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, HLVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	64KB (32K x 16)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	3.8K x 8
Voltage - Supply (Vcc/Vdd)	4.2V ~ 5.5V
Data Converters	A/D 13x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	44-VQFN Exposed Pad
Supplier Device Package	44-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/pic18f4610-e-ml

TABLE 2-1: PIN DESCRIPTIONS (DURING PROGRAMMING): PIC18F2XXX/4XXX FAMILY

Pin Name	During Programming		
	Pin Name	Pin Type	Pin Description
$\overline{MCLR}$/VPP/RE3	VPP	P	Programming Enable
VDD(2)	VDD	P	Power Supply
VSS(2)	VSS	P	Ground
RB5	PGM	I	Low-Voltage ICSP™ Input when LVP Configuration bit equals '1'(1)
RB6	PGC	I	Serial Clock
RB7	PGD	I/O	Serial Data

Legend: I = Input, O = Output, P = Power
Note 1: See Figure 5-1 for more information.
2: All power supply (VDD) and ground (VSS) pins must be connected.

The following devices are included in 28-pin SPDIP, PDIP and SOIC parts:

- PIC18F2221
- PIC18F2321
- PIC18F2410
- PIC18F2420
- PIC18F2423
- PIC18F2450
- PIC18F2455
- PIC18F2458
- PIC18F2480
- PIC18F2510
- PIC18F2515
- PIC18F2520
- PIC18F2523
- PIC18F2525
- PIC18F2550
- PIC18F2553
- PIC18F2580
- PIC18F2585
- PIC18F2610
- PIC18F2620
- PIC18F2680
- PIC18F2682
- PIC18F2685

The following devices are included in 28-pin SSOP parts:

- PIC18F2221
- PIC18F2321

FIGURE 2-1: 28-Pin SPDIP, PDIP, SOIC,SSOP

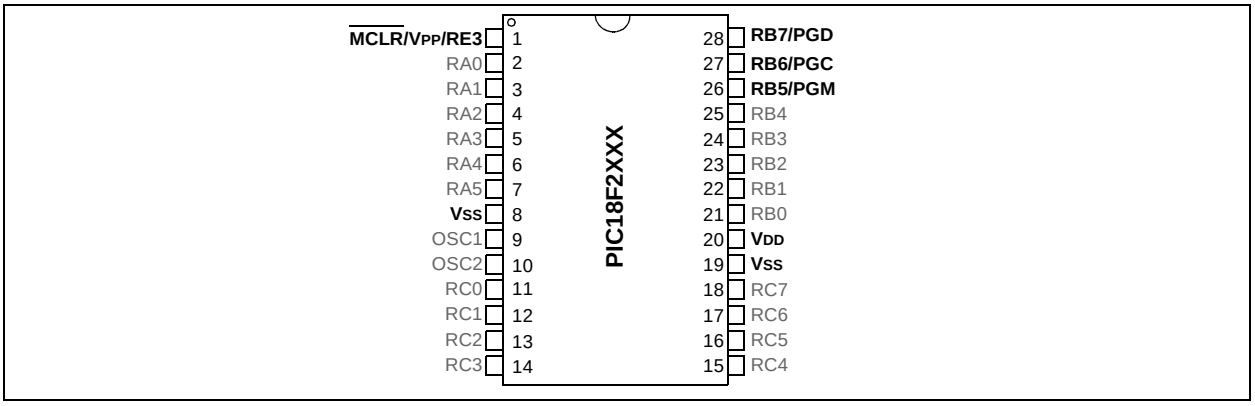
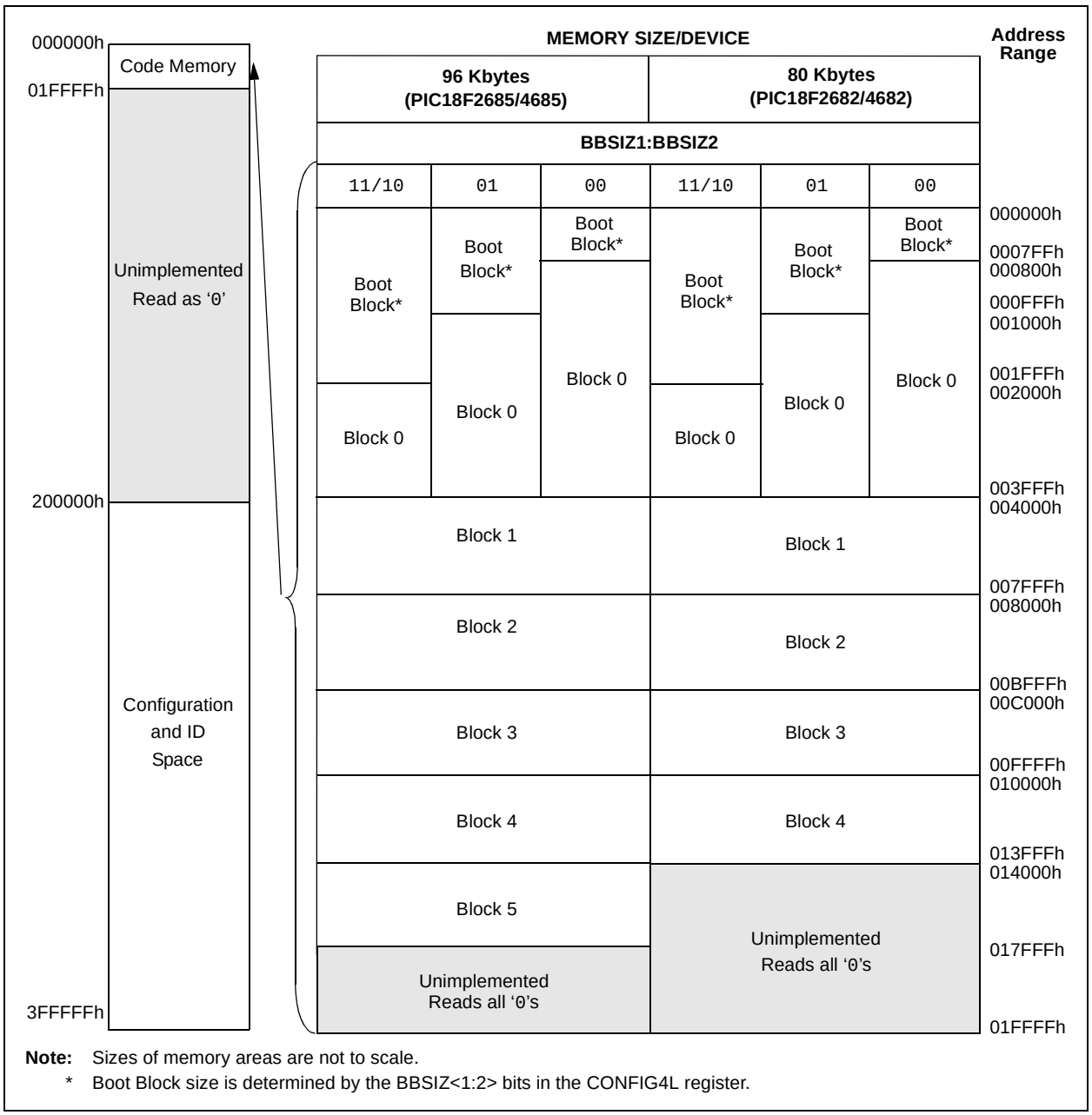


FIGURE 2-7: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F2685/4685 AND PIC18F2682/4682 DEVICES



Note: Sizes of memory areas are not to scale.

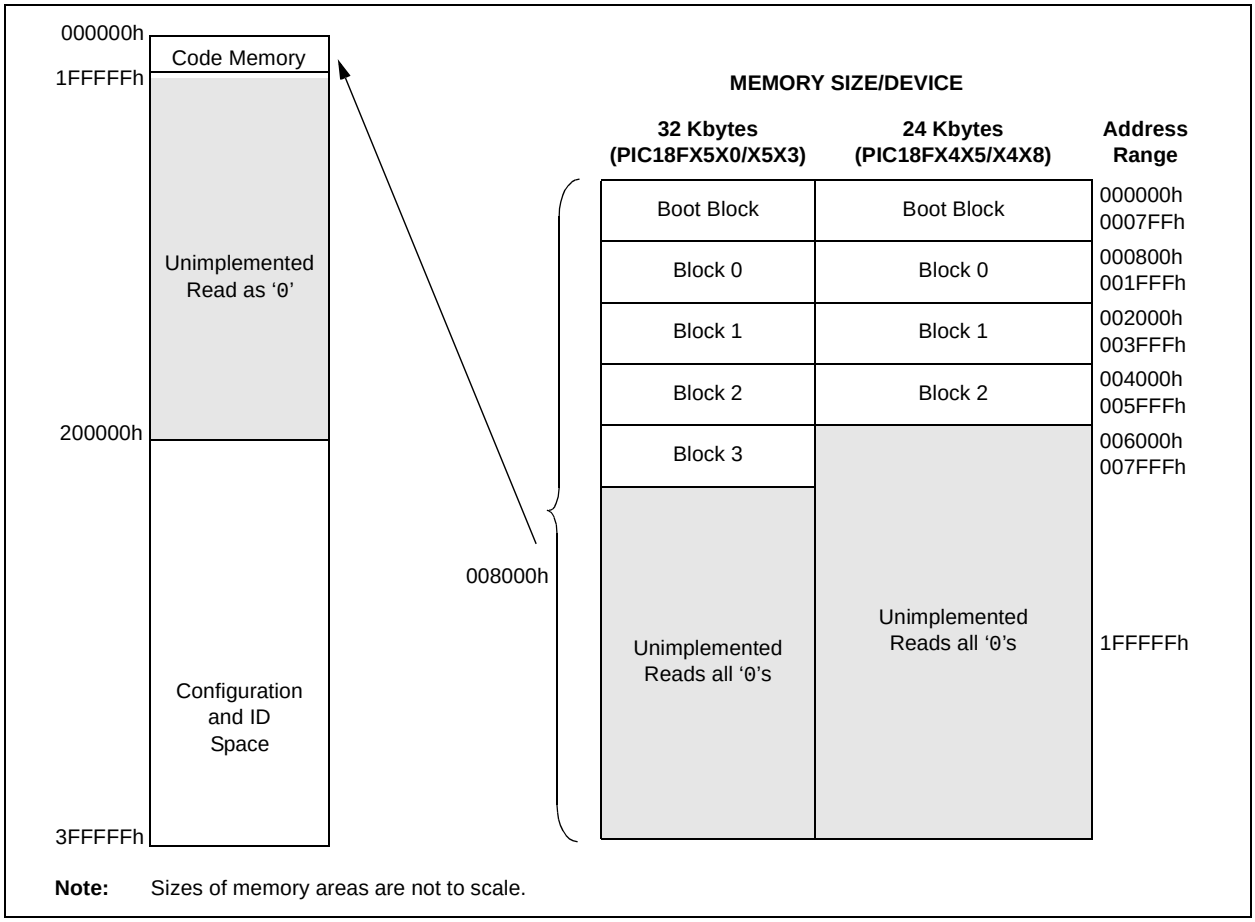
* Boot Block size is determined by the BBSIZ<1:2> bits in the CONFIG4L register.

For PIC18FX5X0/X5X3 devices, the code memory space extends from 000000h to 007FFFh (32 Kbytes) in four 8-Kbyte blocks. For PIC18FX4X5/X4X8 devices, the code memory space extends from 000000h to 005FFFh (24 Kbytes) in three 8-Kbyte blocks. Addresses, 000000h through 0007FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-4: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2455	000000h-005FFFh (24K)
PIC18F2458	
PIC18F4455	
PIC18F4458	
PIC18F2510	000000h-007FFFh (32K)
PIC18F2520	
PIC18F2523	
PIC18F2550	
PIC18F2553	
PIC18F4510	
PIC18F4520	
PIC18F4523	
PIC18F4550	
PIC18F4553	

FIGURE 2-8: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18FX4X5/X4X8/X5X0/X5X3 DEVICES



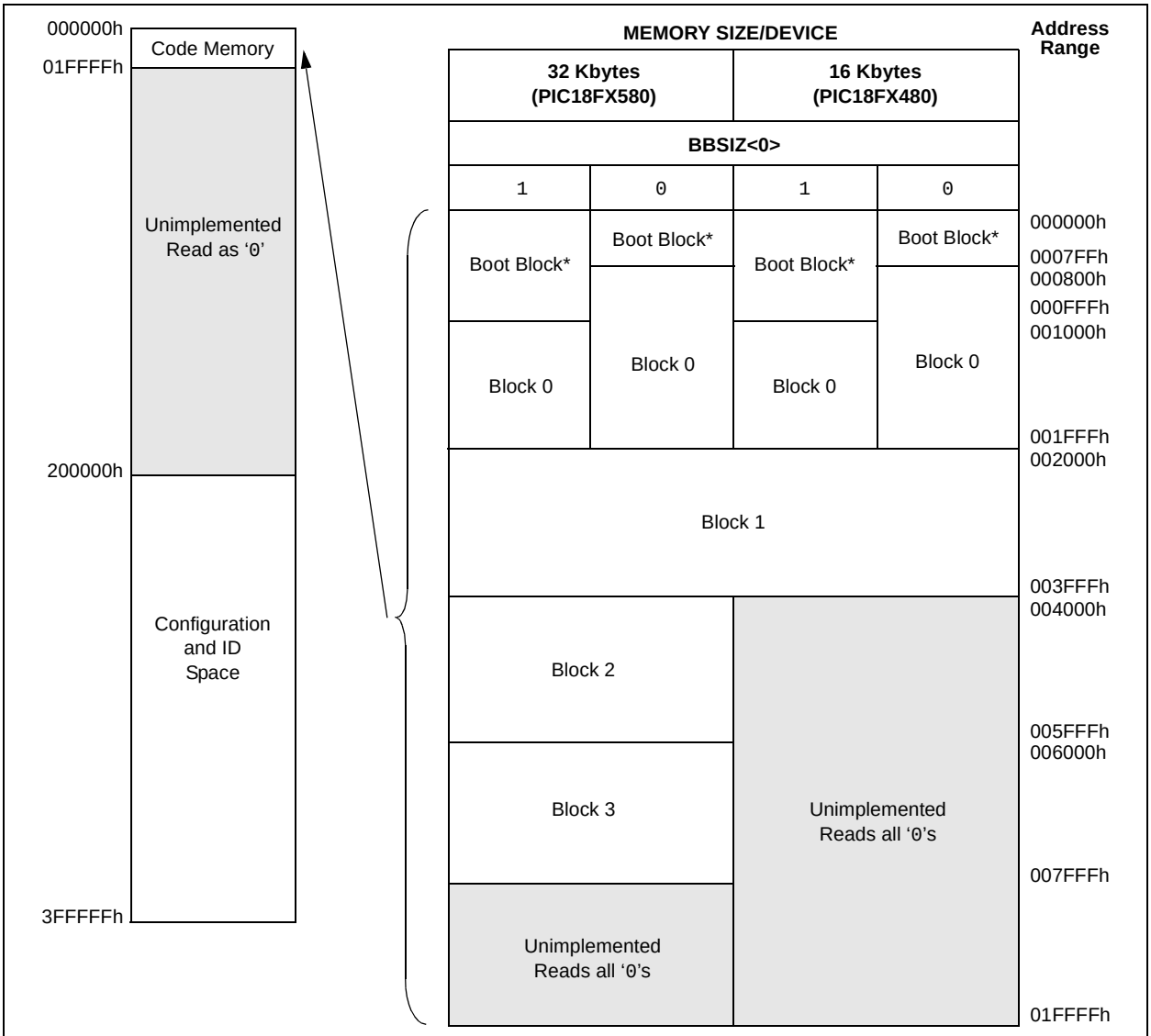
Note: Sizes of memory areas are not to scale.

For PIC18FX4X0/X4X3 devices, the code memory space extends from 000000h to 003FFFh (16 Kbytes) in two 8-Kbyte blocks. Addresses, 000000h through 0003FFh, however, define a “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

TABLE 2-6: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2480	000000h-003FFFh (16K)
PIC18F4480	
PIC18F2580	000000h-007FFFh (32K)
PIC18F4580	

FIGURE 2-10: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F2480/2580/4480/4580 DEVICES



Note: Sizes of memory areas are not to scale.

* Boot Block size is determined by the BBSIZ<0> bit in the CONFIG4L register.

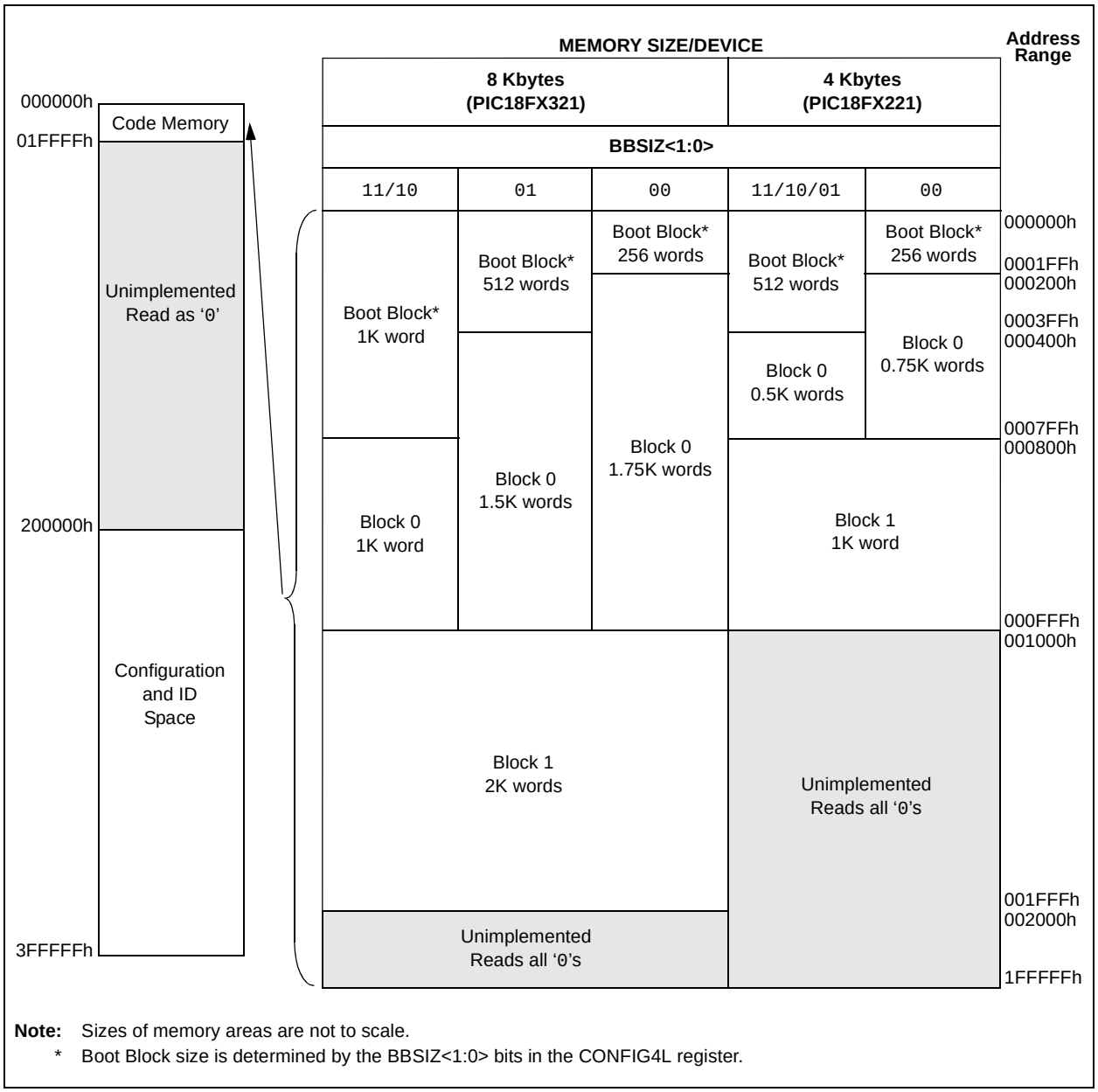
For PIC18F2221/4221 devices, the code memory space extends from 0000h to 00FFFh (4 Kbytes) in one 4-Kbyte block. For PIC18F2321/4321 devices, the code memory space extends from 0000h to 01FFFh (8 Kbytes) in two 4-Kbyte blocks. Addresses, 0000h through 07FFh, however, define a variable “Boot Block” region that is treated separately from Block 0. All of these blocks define code protection boundaries within the code memory space.

The size of the Boot Block in PIC18F2221/2321/4221/4321 devices can be configured as 256, 512 or 1024 words (see Figure 2-11). This is done through the BBSIZ<1:0> bits in the Configuration register, CONFIG4L (see Figure 2-11). It is important to note that increasing the size of the Boot Block decreases the size of Block 0.

TABLE 2-7: IMPLEMENTATION OF CODE MEMORY

Device	Code Memory Size (Bytes)
PIC18F2221	000000h-000FFFh (4K)
PIC18F4221	
PIC18F2321	000000h-001FFFh (8K)
PIC18F4321	

FIGURE 2-11: MEMORY MAP AND THE CODE MEMORY SPACE FOR PIC18F2221/2321/4221/4321 DEVICES



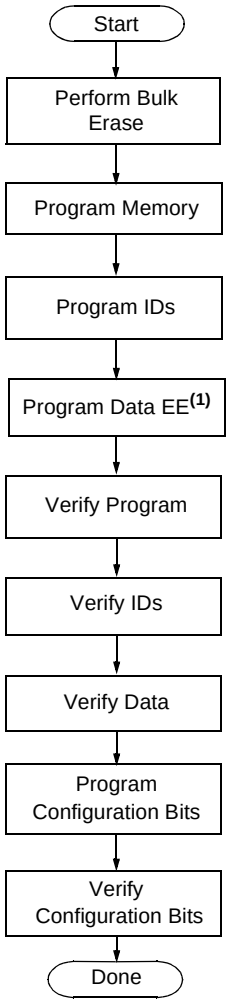
Note: Sizes of memory areas are not to scale.

* Boot Block size is determined by the BBSIZ<1:0> bits in the CONFIG4L register.

2.4 High-Level Overview of the Programming Process

Figure 2-13 shows the high-level overview of the programming process. First, a Bulk Erase is performed. Next, the code memory, ID locations and data EEPROM are programmed (selected devices only, see **Section 3.3 "Data EEPROM Programming"**). These memories are then verified to ensure that programming was successful. If no errors are detected, the Configuration bits are then programmed and verified.

FIGURE 2-13: HIGH-LEVEL PROGRAMMING FLOW



Note 1: Selected devices only, see **Section 3.3 "Data EEPROM Programming"**.

2.5 Entering and Exiting High-Voltage ICSP Program/Verify Mode

As shown in Figure 2-14, the High-Voltage ICSP Program/Verify mode is entered by holding PGC and PGD low and then raising $\overline{MCLR}$/VPP/RE3 to VIHH (high voltage). Once in this mode, the code memory, data EEPROM (selected devices only, see **Section 3.3 "Data EEPROM Programming"**), ID locations and Configuration bits can be accessed and programmed in serial fashion. Figure 2-15 shows the exit sequence.

The sequence that enters the device into the Program/Verify mode places all unused I/Os in the high-impedance state.

FIGURE 2-14: ENTERING HIGH-VOLTAGE PROGRAM/VERIFY MODE

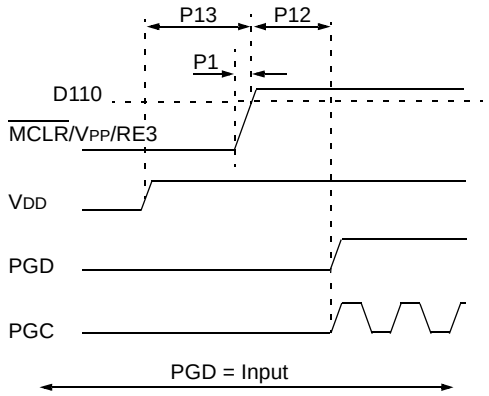
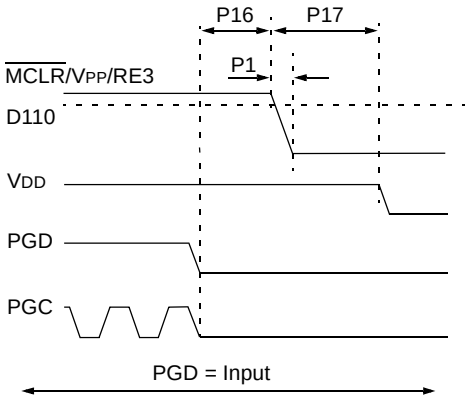


FIGURE 2-15: EXITING HIGH-VOLTAGE PROGRAM/VERIFY MODE



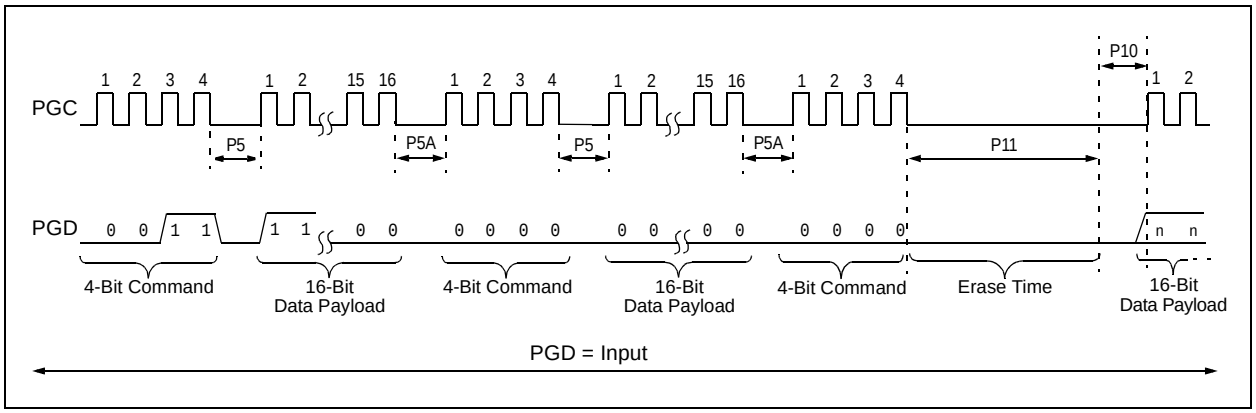
3.1.2 LOW-VOLTAGE ICSP BULK ERASE

When using low-voltage ICSP, the part must be supplied by the voltage specified in Parameter D111 if a Bulk Erase is to be executed. All other Bulk Erase details, as described above, apply.

If it is determined that a program memory erase must be performed at a supply voltage below the Bulk Erase limit, refer to the erase methodology described in **Section 3.1.3 "ICSP Row Erase"** and **Section 3.2.1 "Modifying Code Memory"**.

If it is determined that a data EEPROM erase (selected devices only, see **Section 3.3 "Data EEPROM Programming"**) must be performed at a supply voltage below the Bulk Erase limit, follow the methodology described in **Section 3.3 "Data EEPROM Programming"** and write '1's to the array.

FIGURE 3-2: BULK ERASE TIMING



3.1.3 ICSP ROW ERASE

Regardless of whether high or low-voltage ICSP is used, it is possible to erase one row (64 bytes of data), provided the block is not code or write-protected. Rows are located at static boundaries, beginning at program memory address, 000000h, extending to the internal program memory limit (see **Section 2.3 "Memory Maps"**).

The Row Erase duration is externally timed and is controlled by PGC. After the WR bit in EECON1 is set, a NOP is issued, where the 4th PGC is held high for the duration of the programming time, P9.

After PGC is brought low, the programming sequence is terminated. PGC must be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

The code sequence to Row Erase a PIC18F2XXX/4XXX Family device is shown in Table 3-3. The flowchart, shown in Figure 3-3, depicts the logic necessary to completely erase a PIC18F2XXX/4XXX Family device. The timing diagram that details the Start Programming command and Parameters P9 and P10 is shown in Figure 3-5.

Note:	The TBLPTR register can point to any byte within the row intended for erase.

TABLE 3-3: ERASE CODE MEMORY CODE SEQUENCE

4-Bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory and enable writes.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
0000	84 A6	BSF EECON1, WREN
Step 2: Point to first row in code memory.		
0000	6A F8	CLRF TBLPTRU
0000	6A F7	CLRF TBLPTRH
0000	6A F6	CLRF TBLPTRL
Step 3: Enable erase and erase single row.		
0000	88 A6	BSF EECON1, FREE
0000	82 A6	BSF EECON1, WR
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
Step 4: Repeat Step 3, with the Address Pointer incremented by 64 until all rows are erased.		

FIGURE 3-3: SINGLE ROW ERASE CODE MEMORY FLOW

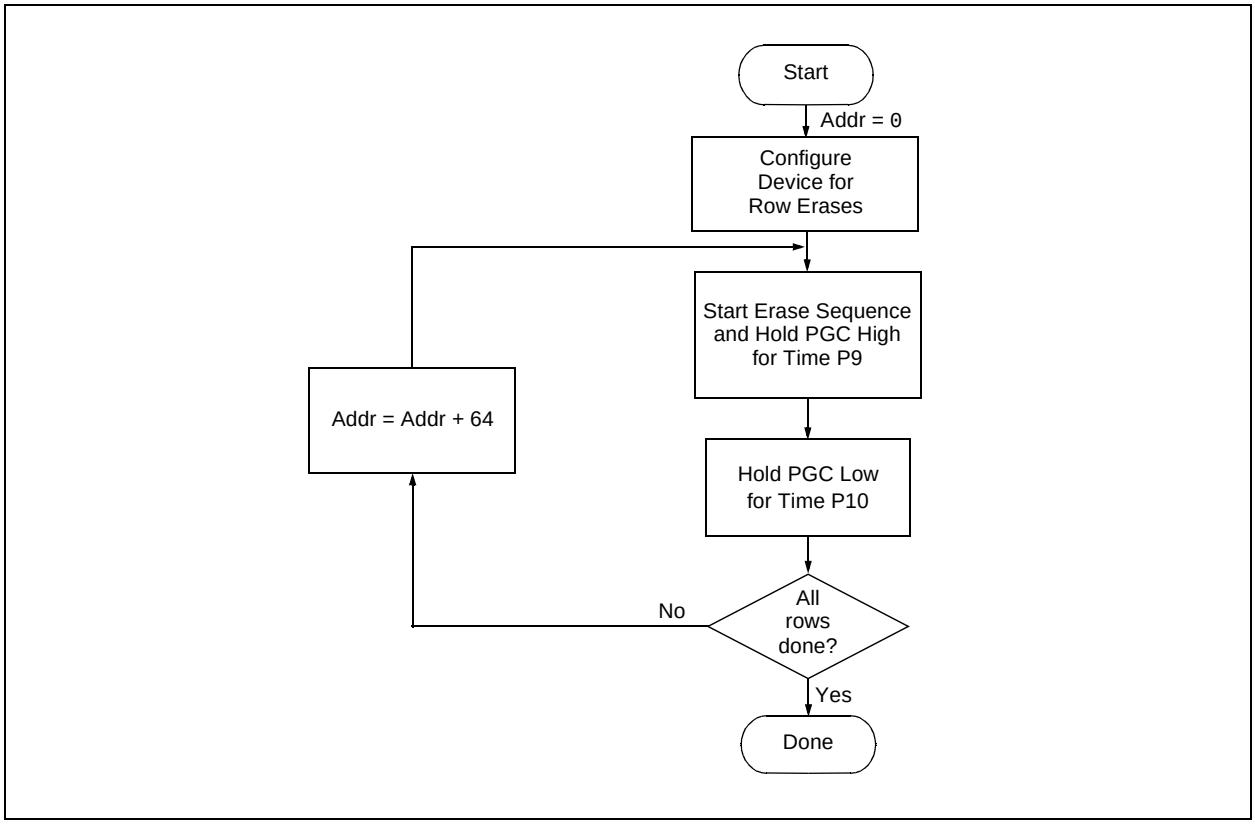


TABLE 3-5: WRITE CODE MEMORY CODE SEQUENCE

4-Bit Command	Data Payload	Core Instruction
Step 1: Direct access to code memory and enable writes.		
0000	8E A6	BSF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Load write buffer.		
0000	0E <Addr[21:16]>	MOVLW <Addr[21:16]>
0000	6E F8	MOVWF TBLPTRU
0000	0E <Addr[15:8]>	MOVLW <Addr[15:8]>
0000	6E F7	MOVWF TBLPTRH
0000	0E <Addr[7:0]>	MOVLW <Addr[7:0]>
0000	6E F6	MOVWF TBLPTRL
Step 3: Repeat for all but the last two bytes.		
1101	<MSB><LSB>	Write 2 bytes and post-increment address by 2.
Step 4: Load write buffer for last two bytes.		
1111	<MSB><LSB>	Write 2 bytes and start programming.
0000	00 00	NOP - hold PGC high for time P9 and low for time P10.
To continue writing data, repeat Steps 2 through 4, where the Address Pointer is incremented by 2 at each iteration of the loop.		

3.3 Data EEPROM Programming

Note: Data EEPROM programming is **not** available on the following devices:	
PIC18F2410	PIC18F4410
PIC18F2450	PIC18F4450
PIC18F2510	PIC18F4510
PIC18F2515	PIC18F4515
PIC18F2610	PIC18F4610

Data EEPROM is accessed one byte at a time via an Address Pointer (register pair: EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is written by loading EEADRH:EEADR with the desired memory location, EEDATA, with the data to be written and initiating a memory write by appropriately configuring the EECON1 register. A byte write automatically erases the location and writes the new data (erase-before-write).

When using the EECON1 register to perform a data EEPROM write, both the EEPGD and CFGS bits must be cleared (EECON1<7:6> = 00). The WREN bit must be set (EECON1<2> = 1) to enable writes of any sort and this must be done prior to initiating a write sequence. The write sequence is initiated by setting the WR bit (EECON1<1> = 1).

The write begins on the falling edge of the 4th PGC after the WR bit is set. It ends when the WR bit is cleared by hardware.

After the programming sequence terminates, PGC must still be held low for the time specified by Parameter P10 to allow high-voltage discharge of the memory array.

FIGURE 3-6: PROGRAM DATA FLOW

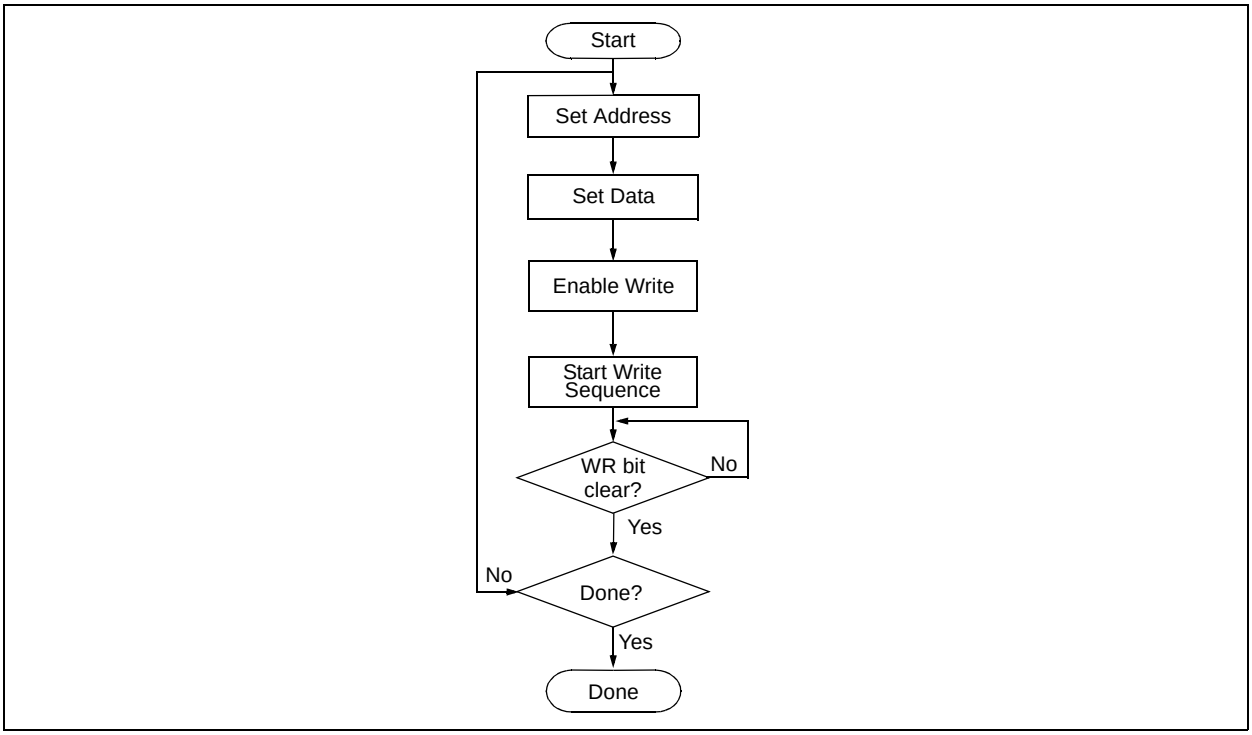


TABLE 3-7: PROGRAMMING DATA MEMORY

4-Bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000	9E A6	BCF EECON1, EEPGD
0000	9C A6	BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000	0E <Addr>	MOVLW <Addr>
0000	6E A9	MOVWF EEADR
0000	OE <AddrH>	MOVLW <AddrH>
0000	6E AA	MOVWF EEADRH
Step 3: Load the data to be written.		
0000	0E <Data>	MOVLW <Data>
0000	6E A8	MOVWF EEDATA
Step 4: Enable memory writes.		
0000	84 A6	BSF EECON1, WREN
Step 5: Initiate write.		
0000	82 A6	BSF EECON1, WR
Step 6: Poll WR bit, repeat until the bit is clear.		
0000	50 A6	MOVF EECON1, W, 0
0000	6E F5	MOVWF TABLAT
0000	00 00	NOP
0010	<MSB><LSB>	Shift out data(1)
Step 7: Hold PGC low for time P10.		
Step 8: Disable writes.		
0000	94 A6	BCF EECON1, WREN
Repeat Steps 2 through 8 to write more data.		

Note 1: See Figure 4-4 for details on shift out data timing.

4.4 Read Data EEPROM Memory

Data EEPROM is accessed, one byte at a time, via an Address Pointer (register pair: EEADRH:EEADR) and a data latch (EEDATA). Data EEPROM is read by loading EEADRH:EEADR with the desired memory location and initiating a memory read by appropriately configuring the EECON1 register. The data will be loaded into EEDATA, where it may be serially output on PGD via the 4-bit command, '0010' (Shift Out Data Holding register). A delay of P6 must be introduced after the falling edge of the 8th PGC of the operand to allow PGD to transition from an input to an output. During this time, PGC must be held low (see Figure 4-4).

The command sequence to read a single byte of data is shown in Table 4-2.

FIGURE 4-3: READ DATA EEPROM FLOW

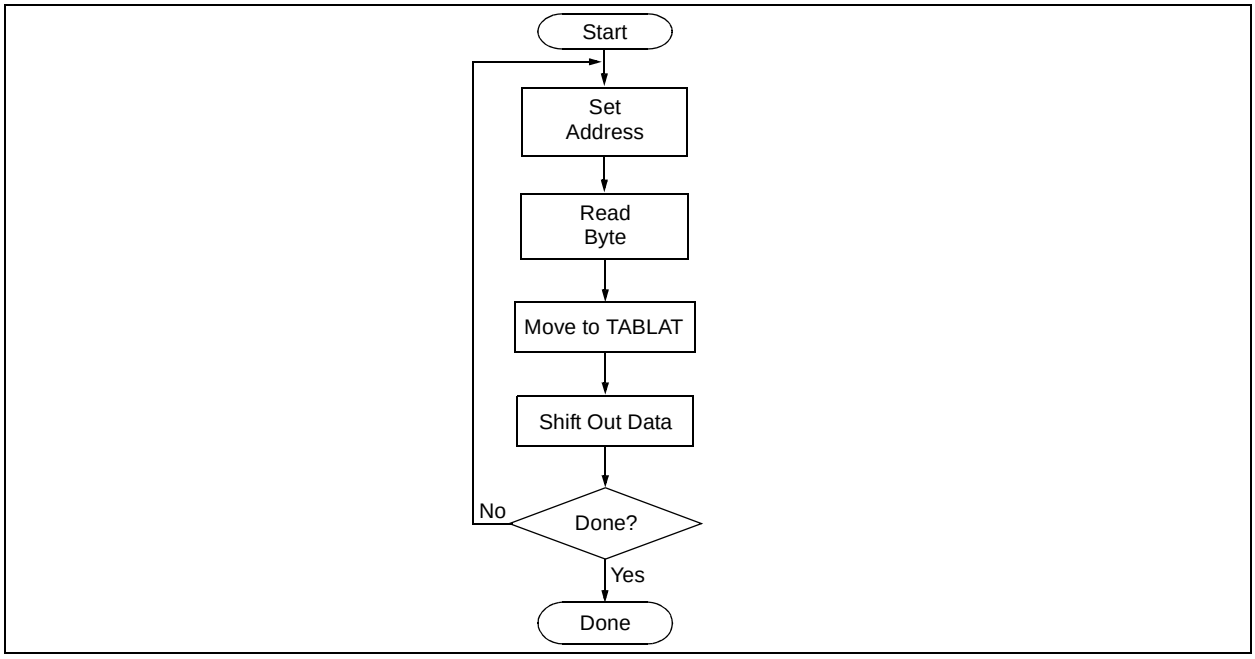


TABLE 4-2: READ DATA EEPROM MEMORY

4-Bit Command	Data Payload	Core Instruction
Step 1: Direct access to data EEPROM.		
0000 0000	9E A6 9C A6	BCF EECON1, EEPGD BCF EECON1, CFGS
Step 2: Set the data EEPROM Address Pointer.		
0000 0000 0000 0000	0E <Addr> 6E A9 OE <AddrH> 6E AA	MOVLW <Addr> MOVWF EEADR MOVLW <AddrH> MOVWF EEADRH
Step 3: Initiate a memory read.		
0000	80 A6	BSF EECON1, RD
Step 4: Load data into the Serial Data Holding register.		
0000 0000 0000 0010	50 A8 6E F5 00 00 <MSB><LSB>	MOVF EEDATA, W, 0 MOVWF TABLAT NOP Shift Out Data(1)

Note 1: The <LSB> is undefined. The <MSB> is the data.

TABLE 5-3: PIC18F2XXX/4XXX FAMILY BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
BBSIZ<1:0>(1)	CONFIG4L	Boot Block Size Select bits **(PIC18F2321/4321 devices only)** 11 = 1K word (2 Kbytes) Boot Block 10 = 1K word (2 Kbytes) Boot Block 01 = 512 words (1 Kbyte) Boot Block 00 = 256 words (512 bytes) Boot Block Boot Block Size Select bits **(PIC18F2221/4221 devices only)** 11 = 512 words (1 Kbyte) Boot Block 10 = 512 words (1 Kbyte) Boot Block 01 = 512 words (1 Kbyte) Boot Block 00 = 256 words (512 bytes) Boot Block
BBSIZ(1)	CONFIG4L	Boot Block Size Select bits **(PIC18F2480/2580/4480/4580 and PIC18F2450/4450 devices only)** 1 = 2K words (4 Kbytes) Boot Block 0 = 1K word (2 Kbytes) Boot Block
LVP	CONFIG4L	Low-Voltage Programming Enable bit 1 = Low-Voltage Programming is enabled, RB5 is the PGM pin 0 = Low-Voltage Programming is disabled, RB5 is an I/O pin
STVREN	CONFIG4L	Stack Overflow/Underflow Reset Enable bit 1 = Reset on stack overflow/underflow is enabled 0 = Reset on stack overflow/underflow is disabled
CP5	CONFIG5L	Code Protection bit (Block 5 code memory area) **(PIC18F2685 and PIC18F4685 devices only)** 1 = Block 5 is not code-protected 0 = Block 5 is code-protected
CP4	CONFIG5L	Code Protection bit (Block 4 code memory area) **(PIC18F2682/2685 and PIC18F4682/4685 devices only)** 1 = Block 4 is not code-protected 0 = Block 4 is code-protected
CP3	CONFIG5L	Code Protection bit (Block 3 code memory area) 1 = Block 3 is not code-protected 0 = Block 3 is code-protected
CP2	CONFIG5L	Code Protection bit (Block 2 code memory area) 1 = Block 2 is not code-protected 0 = Block 2 is code-protected
CP1	CONFIG5L	Code Protection bit (Block 1 code memory area) 1 = Block 1 is not code-protected 0 = Block 1 is code-protected
CP0	CONFIG5L	Code Protection bit (Block 0 code memory area) 1 = Block 0 is not code-protected 0 = Block 0 is code-protected
CPD	CONFIG5H	Code Protection bit (Data EEPROM) 1 = Data EEPROM is not code-protected 0 = Data EEPROM is code-protected
CPB	CONFIG5H	Code Protection bit (Boot Block memory area) 1 = Boot Block is not code-protected 0 = Boot Block is code-protected

Note 1: The BBSIZ bits, BBSIZ<1:0> and BBSIZ<2:1> bits, cannot be changed once any of the following code-protect bits are enabled: CPB or CP0, WRTB or WRT0, EBTRB or EBTR0.

2: Not available in PIC18FXX8X and PIC18F2450/4450 devices.

TABLE 5-3: PIC18F2XXX/4XXX FAMILY BIT DESCRIPTIONS (CONTINUED)

Bit Name	Configuration Words	Description
WRT5	CONFIG6L	Write Protection bit (Block 5 code memory area) **(PIC18F2685 and PIC18F4685 devices only)** 1 = Block 5 is not write-protected 0 = Block 5 is write-protected
WRT4	CONFIG6L	Write Protection bit (Block 4 code memory area) **(PIC18F2682/2685 and PIC18F4682/4685 devices only)** 1 = Block 4 is not write-protected 0 = Block 4 is write-protected
WRT3	CONFIG6L	Write Protection bit (Block 3 code memory area) 1 = Block 3 is not write-protected 0 = Block 3 is write-protected
WRT2	CONFIG6L	Write Protection bit (Block 2 code memory area) 1 = Block 2 is not write-protected 0 = Block 2 is write-protected
WRT1	CONFIG6L	Write Protection bit (Block 1 code memory area) 1 = Block 1 is not write-protected 0 = Block 1 is write-protected
WRT0	CONFIG6L	Write Protection bit (Block 0 code memory area) 1 = Block 0 is not write-protected 0 = Block 0 is write-protected
WRTD	CONFIG6H	Write Protection bit (Data EEPROM) 1 = Data EEPROM is not write-protected 0 = Data EEPROM is write-protected
WRTB	CONFIG6H	Write Protection bit (Boot Block memory area) 1 = Boot Block is not write-protected 0 = Boot Block is write-protected
WRTC	CONFIG6H	Write Protection bit (Configuration registers) 1 = Configuration registers are not write-protected 0 = Configuration registers are write-protected
EBTR5	CONFIG7L	Table Read Protection bit (Block 5 code memory area) **(PIC18F2685 and PIC18F4685 devices only)** 1 = Block 5 is not protected from Table Reads executed in other blocks 0 = Block 5 is protected from Table Reads executed in other blocks
EBTR4	CONFIG7L	Table Read Protection bit (Block 4 code memory area) **(PIC18F2682/2685 and PIC18F4682/4685 devices only)** 1 = Block 4 is not protected from Table Reads executed in other blocks 0 = Block 4 is protected from Table Reads executed in other blocks
EBTR3	CONFIG7L	Table Read Protection bit (Block 3 code memory area) 1 = Block 3 is not protected from Table Reads executed in other blocks 0 = Block 3 is protected from Table Reads executed in other blocks
EBTR2	CONFIG7L	Table Read Protection bit (Block 2 code memory area) 1 = Block 2 is not protected from Table Reads executed in other blocks 0 = Block 2 is protected from Table Reads executed in other blocks
EBTR1	CONFIG7L	Table Read Protection bit (Block 1 code memory area) 1 = Block 1 is not protected from Table Reads executed in other blocks 0 = Block 1 is protected from Table Reads executed in other blocks

Note 1: The BBSIZ bits, BBSIZ<1:0> and BBSIZ<2:1> bits, cannot be changed once any of the following code-protect bits are enabled: CPB or CP0, WRTB or WRT0, EBTRB or EBTR0.

2: Not available in PIC18FXX8X and PIC18F2450/4450 devices.

TABLE 5-5: CONFIGURATION WORD MASKS FOR COMPUTING CHECKSUMS

Device	Configuration Word (CONFIGxx)													
	1L	1H	2L	2H	3L	3H	4L	4H	5L	5H	6L	6H	7L	7H
	Address (30000xh)													
	0h	1h	2h	3h	4h	5h	6h	7h	8h	9h	Ah	Bh	Ch	Dh
PIC18F2221	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F2321	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F2410	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2420	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2423	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F2450	3F	CF	3F	1F	00	86	ED	00	03	40	03	60	03	40
PIC18F2455	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F2458	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F2480	00	CF	1F	1F	00	86	D5	00	03	C0	03	E0	03	40
PIC18F2510	00	1F	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2515	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2520	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2523	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2525	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2550	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F2553	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F2580	00	CF	1F	1F	00	86	D5	00	0F	C0	0F	E0	0F	40
PIC18F2585	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F2610	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2620	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F2680	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F2682	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F2685	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F4221	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F4321	00	CF	1F	1F	00	87	F5	00	03	C0	03	E0	03	40
PIC18F4410	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F4420	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F4423	00	CF	1F	1F	00	87	C5	00	03	C0	03	E0	03	40
PIC18F4450	3F	CF	3F	1F	00	86	ED	00	03	40	03	60	03	40
PIC18F4455	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F4458	3F	CF	3F	1F	00	87	E5	00	07	C0	07	E0	07	40
PIC18F4480	00	CF	1F	1F	00	86	D5	00	03	C0	03	E0	03	40
PIC18F4510	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4515	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4520	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4523	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4525	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4550	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F4553	3F	CF	3F	1F	00	87	E5	00	0F	C0	0F	E0	0F	40
PIC18F4580	00	CF	1F	1F	00	86	D5	00	0F	C0	0F	E0	0F	40
PIC18F4585	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F4610	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40

Legend: Shaded cells are unimplemented.

TABLE 5-5: CONFIGURATION WORD MASKS FOR COMPUTING CHECKSUMS (CONTINUED)

Device	Configuration Word (CONFIGxx)													
	1L	1H	2L	2H	3L	3H	4L	4H	5L	5H	6L	6H	7L	7H
	Address (30000xh)													
	0h	1h	2h	3h	4h	5h	6h	7h	8h	9h	Ah	Bh	Ch	Dh
PIC18F4620	00	CF	1F	1F	00	87	C5	00	0F	C0	0F	E0	0F	40
PIC18F4680	00	CF	1F	1F	00	86	C5	00	0F	C0	0F	E0	0F	40
PIC18F4682	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40
PIC18F4685	00	CF	1F	1F	00	86	C5	00	3F	C0	3F	E0	3F	40

Legend: Shaded cells are unimplemented.

6.0 AC/DC CHARACTERISTICS TIMING REQUIREMENTS FOR PROGRAM/VERIFY TEST MODE

Standard Operating Conditions
Operating Temperature: 25°C is recommended

Param No.	Sym	Characteristic	Min	Max	Units	Conditions
D110	VIHH	High-Voltage Programming Voltage on MCLR/VPP/RE3	VDD + 4.0	12.5	V	**(Note 2)**
D110A	VIHL	Low-Voltage Programming Voltage on MCLR/VPP/RE3	2.00	5.50	V	**(Note 2)**
D111	VDD	Supply Voltage During Programming	2.00	5.50	V	Externally timed, Row Erases and all writes
			3.0	5.50	V	Self-timed, Bulk Erases only **(Note 3)**
D112	IPP	Programming Current on MCLR/VPP/RE3	—	300	μA	**(Note 2)**
D113	IDDP	Supply Current During Programming	—	10	mA	
D031	VIL	Input Low Voltage	VSS	0.2 VDD	V	
D041	VIH	Input High Voltage	0.8 VDD	VDD	V	
D080	VOL	Output Low Voltage	—	0.6	V	IOL = 8.5 mA @ 4.5V
D090	VOH	Output High Voltage	VDD – 0.7	—	V	IOH = -3.0 mA @ 4.5V
D012	CIO	Capacitive Loading on I/O pin (PGD)	—	50	pF	To meet AC specifications
P1	TR	MCLR/VPP/RE3 Rise Time to Enter Program/Verify mode	—	1.0	μs	**(Notes 1, 2)**
P2	TPGC	Serial Clock (PGC) Period	100	—	ns	VDD = 5.0V
			1	—	μs	VDD = 2.0V
P2A	TPGCL	Serial Clock (PGC) Low Time	40	—	ns	VDD = 5.0V
			400	—	ns	VDD = 2.0V
P2B	TPGCH	Serial Clock (PGC) High Time	40	—	ns	VDD = 5.0V
			400	—	ns	VDD = 2.0V
P3	TSET1	Input Data Setup Time to Serial Clock ↓	15	—	ns	
P4	THLD1	Input Data Hold Time from PGC ↓	15	—	ns	
P5	TDLY1	Delay Between 4-Bit Command and Command Operand	40	—	ns	
P5A	TDLY1A	Delay Between 4-Bit Command Operand and Next 4-Bit Command	40	—	ns	
P6	TDLY2	Delay Between Last PGC ↓ of Command Byte to First PGC ↑ of Read of Data Word	20	—	ns	
P9	TDLY5	PGC High Time (minimum programming time)	1	—	ms	Externally timed
P10	TDLY6	PGC Low Time After Programming (high-voltage discharge time)	100	—	μs	
P11	TDLY7	Delay to Allow Self-Timed Data Write or Bulk Erase to Occur	5	—	ms	

Note 1: Do not allow excess time when transitioning MCLR between VIL and VIHH. This can cause spurious program executions to occur. The maximum transition time is:
1 TCY + TPWRT (if enabled) + 1024 TOSC (for LP, HS, HS/PLL and XT modes only) +
2 ms (for HS/PLL mode only) + 1.5 μs (for EC mode only)
where TCY is the instruction cycle time, TPWRT is the Power-up Timer period and TOSC is the oscillator period. For specific values, refer to the Electrical Characteristics section of the device data sheet for the particular device.

2: When ICPRT = 1, this specification also applies to ICVPP.

3: At 0°C-50°C.

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